

Cambridge University Press

978-1-107-41364-1 - Materials Research Society Symposium Proceedings: Volume 512:
Wide-Bandgap Semiconductors for High Power, High Frequency and High Temperature
Editors: Steven DenBaars, John Palmour, Michael Shur and Michael Spencer

Index

[More information](#)

AUTHOR INDEX

- Abernathy, C.R., 463, 501, 525
 Agarwal, Q., 41
 Akasaki, Isamu, 181
 Albrecht, M., 543
 Amano, Hiroshi, 181
 Andreev, A., 131
 Aptowitz, K., 137
 Ashby, C.I.H., 487
- Baba, Takaaki, 291
 Badi, H., 285
 Bailey, C., 519
 Bakowski, M., 157
 Baliga, B. Jayant, 77
 Balogh, Adam Q., 261
 Bandic, Z.Z., 27, 387
 Barton, Daniel L., 205
 Basu, S.M., 431
 Batson, P.J., 393
 Beach, R.A., 27
 Beaumont, B., 21, 273, 333
 Benamara, M., 363
 Bensaoula, A., 285
 Berichev, I., 285
 Bidnyk, S., 199
 Bishop, S.Q., 381
 Blant, A.V., 519
 Bouille, A., 273
 Bour, D.P., 531
 Brady, M.F., 89
 Breitholtz, Bo, 151
 Bridger, P.M., 27, 387
 Bridges, M.M., 487
 Brillson, L.J., 137
 Burger, A., 339
 Burton, J.C., 297
 Buzynin, A.N., 417
 Buzynin, Yu.N., 417
 Byeon, D-S., 143
- Cao, X.A., 463
 Carter, Jr., C.H., 89, 119
 Cerrina, F., 393
 Chae, Su Hee, 495
 Chaudhuri, J., 169, 315
 Chen, E., 437
 Chen, F., 303
 Chen, H., 303, 339, 375
 Chen, P., 65, 303
 Chen, Q., 309
 Chen, Youcun, 233
 Chen, Z.Z., 65, 303
 Cheng, T.S., 519
 Cherenkov, A., 451
 Cho, Hyun, 501, 507
 Cho, Y., 393
 Cho, Yong-Hoon, 199, 267
 Choi, Won-Jin, 47
- Choi, Y-L, 143, 175
 Christiansen, S., 543
 Chu, Kenneth, 3
 Chumbes, E.M., 59
 Coleman, J.J., 381
 Collins, W.E., 339, 375
 Contreras, S., 21
- Dapkus, P. Daniel, 47, 193
 Davidov, V., 451
 Davies, T., 333
 Davis, R.F., 437, 475
 Demangeot, F., 333
 DenBaars, S.P., 199, 267, 411
 Dent, A.J., 519
 Dimitrijević, S., 223
 Dmitriev, V., 131, 451
 Donovan, S.M., 501, 525
 Doppalapudi, D., 431
 Drizhuk, A.Q., 513
 Drummond, T.J., 463
 Dudley, M., 107
 Dyakonova, M.V., 21, 211
- Eastman, Lester F., 3, 549, 555
 Edgar, J.H., 169
- Fazi, C., 107
 Feng, Z.C., 297
 Ferguson, I., 297
 Fjeldly, T.A., 9
 Fleming, J.Q., 53
 Follstaedt, D.M., 53
 Foutz, B.E., 549, 555
 Foxon, C.T., 519
 Frandon, J., 333
 Fries-Carr, S., 255
 Frischholz, Manfred, 157, 469
 Fu, M., 463
- Qao, Y., 169
 Qaska, R., 9, 15, 309
 Qelmont, B.L., 549
 Qibart, P., 21
 Qila, B., 525
 Glass, R.C., 89
 Qotoh, Keisuke, 405
 Qovorkov, A.V., 239, 537
 Qradinaru, Q., 309
 Qrandjean, N., 69, 333
 Grow, J.M., 507
 Grzegory, I., 363
- Haffouz, S., 273
 Hallen, Anders, 151, 469
 Han, J., 53, 463, 487, 501, 507
 Han, Min-Koo, 143, 175
 Harris, Jr., James S., 291

Cambridge University Press

978-1-107-41364-1 - Materials Research Society Symposium Proceedings: Volume 512:
Wide-Bandgap Semiconductors for High Power, High Frequency and High Temperature
Editors: Steven DenBaars, John Palmour, Michael Shur and Michael Spencer

Index

[More information](#)

- Harrison, H.B., 223
Harrison, P.G., 519
Hecht, C., 369
Heidger, S., 255
Henkel, T., 163
Henry, R.L., 315
Henshall, D.N., 89
Hersee, Steve, 399
Hill, D.N., 41
Holländer, B., 543
Huang, W., 107
Hunn, J., 475
- Ignatiev, K., 169
Iota, Valentin, 399
Irene, E., 475
Irvine, K.G., 119
Isaacs-Smith, T., 101
Ishida, Masahiro, 291
Itoh, Kunio, 291
- Jansson, U., 125
Jeffs, N.J., 519
Johnson, N.M., 531
Johri, D., 357
Jordan, B., 255
- Kamp, M., 543
Kao, N.C., 309
Karlsson, Stefan, 469
Keller, S., 199, 267
Khan, M.A., 309
Khim, Jin Seok, 495
Khlebnikov, I., 351
Kim, D-Y., 175
Kim, E., 285
Kim, Hyon-Soo, 495
Kim, S., 381
Kim, Tae Il, 495
Kim, Taek, 495
Kim, Y., 393
Kirchner, C., 543
Kisielowski, Christian, 187, 393, 399
Knap, W., 21
Kneissl, M., 531
Kobayashi, Junko T., 47, 193
Kobayashi, N., 163
Kobayashi, Nobuhiko P., 47, 193
Kobayashi, Takeshi, 217
Kohl, P.A., 227
Koitzsch, C., 357
Koleske, D.D., 315
Konstantinov, Andrey O., 151
Kordina, O., 119
Koutzarov, I., 163
Kovarsky, A., 451
Krasinski, J., 199
Krasnobaev, L., 475
Kropewnicki, T.J., 227
Krueger, J., 393
Kruger, Joachim, 187
Kuball, M., 333
- Kuech, T.F., 321, 327
Kummer, R., 369
Kuznetsov, N., 131, 451
- Lamb, H.H., 437
Lambers, E.S., 507
Lebedev, O.I., 481
Lee, J.W., 487
Lee, Jinhyun, 205
Lee, K.N., 525
Lee, You-Sang, 143, 175
Léotin, J., 333
Leroux, M., 69, 273
Lester, L.F., 487
Levinshtein, M.E., 21, 211
Li, H.F., 223
Li, J., 297
Li, X., 381
Liliental-Weber, Z., 363
Lin, Zhangda, 233
Lo, Y.H., 59
Lomonova, E.E., 417
Long, F.H., 297
Lorenzini, P., 69
Lorusso, G.F., 393
Lu, W., 339, 375
Lundin, W.V., 513
- MacKenzie, J.D., 501, 525
Madangarli, V.P., 101, 345, 351
Maeda, T., 501
Maki, Tetsuro, 217
Mantl, S., 543
Mascher, Peter, 261
Massies, J., 69
Mattos, Laila, 187
Mayer, M., 543
McCluskey, M.D., 531
McGill, T.C., 27, 387
Medelci, N., 285
Mesrine, M., 69
Michel, A., 437
Minbaeva, M., 131
Mishra, U.K., 199, 267
Mohney, S.E., 279
Mönch, W., 457
Morozov, A., 131
Mosselmans, J.F.W., 519
Moustakas, T.D., 431
Muhr, G.T., 525
- Nakamura, S., 363
Nam, O., 437
Nause, J.E., 41
Nemanich, R., 357
Neudeck, P.G., 107
Ng, M. Hooe, 315
Nikitina, I., 451
Nikolaev, A., 451
Nordgren, K., 157
Norin, L., 125

Cambridge University Press

978-1-107-41364-1 - Materials Research Society Symposium Proceedings: Volume 512:
Wide-Bandgap Semiconductors for High Power, High Frequency and High Temperature
Editors: Steven DenBaars, John Palmour, Michael Shur and Michael Spencer

Index

[More information](#)

- O'Brien, M., 357
 Oder, T.N., 101
 Oh, J.-K., 175
 Ohshima, Naoki, 405
 Ohshima, T., 163
 Okumura, H., 163
 O'Leary, S.K., 549, 555
 Osiko, V.V., 417
 Osiriski, Marek, 205
 Osinsky, A., 15
 Östling, M., 125, 507

 Paisley, M.J., 119
 Palmour, J.W., 119, 211
 Parikh, N., 475
 Park, I.-Y., 143
 Pearton, S.J., 463, 487, 501, 507
 Pelzmann, A., 543
 Perkins, N., 321
 Perlin, Piotr, 187, 399
 Phanse, V.M., 27
 Piquette, E.C., 27, 387
 Pirouz, P., 113
 Polyakov, A.Y., 239, 537
 Ponnambalam, V., 245, 249, 423
 Pophristic, M., 297
 Porowski, S., 363
 Price, K., 475
 Puff, Werner, 261
 Pushnyi, B.V., 513

 Rastegaeva, M., 131
 Redwing, J.M., 27, 239, 537
 Ren, F., 501, 507
 Rendakova, S., 131
 Renucci, M.A., 333
 Rhee, S.J., 381
 Rich, D.H., 193
 Richardson, H.H., 445
 Richter, O., 363
 Rieger, D.J., 463
 Rohleder, M., 457
 Rottner, Kurt, 157, 469
 Rumyantsev, S.L., 211

 Sarvepalli, V., 463
 Savkina, N., 131
 Schmitt, T.J., 199
 Schmitt, Thomas, 469
 Schöner, Adolf, 157, 469
 Seidel, J., 157
 Sekhar, J.A., 463
 Serra, A.D., 445
 Shapiro, Noad A., 187
 Shealy, J. Richard, 3, 59
 Shen, B., 65, 303
 Shi, D.T., 339, 375
 Shul, R.J., 463, 487, 501, 507
 Shur, M.S., 9, 15, 549, 555
 Sidorov, D.V., 513
 Sidorov, V.G., 513
 Singh, R., 119, 211

 Singh, R.K., 463
 Slack, Glen A., 35
 Smart, Joseph A., 3, 59
 Smirnov, D., 333
 Smirnov, N.B., 239, 537
 Solak, H., 393
 Soloviev, S., 351
 Song, J.J., 199, 267
 Srivatsa, L.N., 59
 Starikov, D., 285
 Steeds, J.W., 333
 Stepanov, S., 451
 Stoltz, A., 357
 Stroschio, M., 549
 Strunk, H.P., 543
 Sudarshan, T.S., 101, 309, 345, 351
 Sun, L., 297
 Sun, X.T., 303
 Suski, Tadeusz, 399
 Suvkhanov, A., 475
 Suvorov, A.V., 481
 Suvorova, A.A., 481
 Sweatman, D., 223
 Swider, W., 363

 Takayama, Toru, 291
 Takeuchi, Tetsuya, 181
 Tanaka, Hiroyuki, 217
 Tanaka, Y., 163
 Tanner, P., 223
 Teisseyre, Henryk, 399
 Tempez, A., 285
 Thomson, D., 437, 475
 Tin, C.C., 101, 345
 Tsvetkov, D., 451
 Tsvetkov, V.F., 89

 Ueda, Tetsuzo, 291
 Uesugi, Shinobu, 405
 Underwood, J.H., 393
 Usikov, A.S., 417, 513
 Usov, I.O., 481

 Van de Walle, C.G., 531
 van Elsbergen, V., 457
 Van Tendeloo, G., 481
 Varadaraju, U.V., 245, 249, 423
 Vaudo, R.P., 27
 Vennegues, P., 273
 Venugopalan, H.S., 279

 Walukiewicz, W., 531
 Wang, J.J., 507
 Wang, M., 65
 Washburn, J., 363
 Weber, Eicke R., 187, 393, 399
 Weimer, J., 255
 Weinstein, Bernie A., 399
 Wetzel, Christian, 181
 Wickenden, A.E., 315
 Williams, J.R., 101
 Willison, C.G., 487

Wilson, R.G., 463, 525	Yoshida, S., 163
Winnacker, A., 369	
Wu, R., 255	Young, A.P., 137
Wu, W., 475	Yun, Young, 217
Wu, Z.S., 303	Yuri, Masaaki, 291
Xie, Fangqing, 233	Zavada, J.M., 411
Xie, Z.Y., 169	Zetterling, C-M., 125, 507
	Zhang, L., 65, 303, 321, 487
Yagovkina, M., 451	Zhang, Qingzhe, 233
Yamahira, Seiji, 405	Zhang, Rong, 65, 303, 321, 327
Yan, C.H., 411	Zhang, X.Y., 303
Yang, Jinwei, 9, 187, 309, 363, 399	Zhang, Xingang, 193
Yang, K., 303	Zheng, Y.D., 65, 303
Yao, H., 411	Zhou, Y.G., 65, 303
Yeom, Geun-Young, 495	Zimmermann, Uwe, 151
Yonezu, Hiroo, 405	Zolper, J.C., 463

Cambridge University Press

978-1-107-41364-1 - Materials Research Society Symposium Proceedings: Volume 512:
Wide-Bandgap Semiconductors for High Power, High Frequency and High Temperature
Editors: Steven DenBaars, John Palmour, Michael Shur and Michael Spencer

Index

[More information](#)

SUBJECT INDEX

- activation energy, 249
- aluminum nitride, 35, 345, 387, 405, 437, 445, 501
- annealing, 381
- barium lead bismuth oxide, 423
- boron nitride, 285
- breakdown, 15, 101, 107, 151, 309, 345, 351
- CBED, 363
- chemical vapor deposition, 47, 53, 65, 119, 169, 233, 239, 255, 393, 417, 445, 513, 537
- defects, 261, 315, 351, 369, 543
- detector, 15
- diamond, 255
 - nucleation, 233
- doping 297, 327
- etching, 487, 495, 501, 507
- field-effect transistor, 3, 77, 217, 309, 519, 555
- frequency response, 3
- gallium nitride, 3, 21, 27, 41, 47, 53, 59, 65, 69, 113, 181, 187, 193, 199, 227, 239, 267, 273, 279, 285, 291, 303, 309, 315, 321, 327, 333, 381, 387, 393, 399, 411, 417, 431, 437, 451, 457, 463, 469, 487, 495, 501, 513, 519, 531, 537, 543, 549, 555
 - platelet crystals, 363
- growth, 35, 41, 47, 53, 59, 65, 69, 169, 387, 405
- HREM study, 481
- illumination, 21
- impact ionization, 143
- implantation, 469
- indium nitride, 501, 525
- ion implantation, 321, 475, 481
- micropipes, 89, 107, 113, 131, 151
- molecular-beam epitaxy, 69, 387, 405, 431, 519, 525
- molybdenum, 249
- noise, 21
- ohmic contacts, 125
- phonons, 333
- piezoelectric effects, 69, 181, 189
- polarity of GaN, 363
- power factor, 245, 249
- quantum
 - dots, 65
 - wells, 69, 181, 187, 193, 199, 267, 399
- reactive ion etching, 285
- RuAl₃, 245
- Schottky
 - contacts, 125
 - diodes, 175, 279
- silicon carbide, 77, 89, 101, 107, 113, 119, 125, 131, 143, 151, 157, 163, 169, 175, 211, 223, 261, 297, 309, 339, 351, 357, 369, 375, 437, 457, 469, 481, 507
- single crystal, 35, 41
- substrates, 41, 47, 53, 227, 405, 417
- surface chemistry, 233
- TEM, 481
- thermal annealing, 163
- thermopower, 249
- transmission electron microscopy, 273
- transport, 27, 549, 555
- traps, 223, 303, 309
- vapor-phase epitaxy, 27, 59, 113, 273, 315, 321, 327, 451, 513
- zinc oxide, 41